IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: Bradley J. Howard

Filed: Herewith

For: PROCESS FOR USING PHOTO-DEFINABLE LAYERS IN THE MANUFACTURE

OF SEMICONDUCTOR DEVICES AND RESULTING STRUCTURES OF SAME

Serial No.: Unknown

Group Art Unit: Unknown

Examiner: Unknown Atty Dkt: 97-0008.02

Pursuant to 37 C.F.R. 1.8, I certify that this correspondence is being deposited with the U.S. Postal Service in a first class, postage prepaid envelope addressed to: Assistant Commissioner for Patents, Washington, D.C. 20231 on the date below:

11-6-03

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Name

INFORMATION DISCLOSURE STATEMENT

Assistant Commissioner for Patents Washington, D.C. 20231

Sir:

Pursuant to 37 C.F.R. §§ 1.56, 1.97, and 1.98, it is respectfully requested that this Information Disclosure Statement be entered and the documents listed on attached Form PTO-1449 be considered by the Examiner and made of record.

In accordance with 37 C.F.R §§ 1.97(g),(h), this Information Disclosure Statement is not to be construed as a representation that a search has been made, and is not to be construed to be an admission that (a) the information cited is, or is considered to be, material to patentability as defined in 37 C.F.R. § 1.56(b); and/or (b) that the information cited is, or is considered to be prior art.

The present Information Disclosure Statement is being filed prior to the receipt of a first Official Action reflecting an examination on the merits, and hence is believed to be timely filed in accordance with 37 C.F.R. § 1.97(b). No fees are believed to be due in connection with the filing of this Information Disclosure Statement, however, should any fees under 37 C.F.R. §§ 1.16 to 1.21 be deemed necessary for any reason relating to these materials, the Commissioner is hereby authorized to deduct said fees from Deposit Account No. 10-1205.

Copies of the listed documents required by 37 C.F.R. § 1.98(a)(2) have been previously submitted in the parent application.

Applicant respectfully requests that the listed documents be made of record in the present case.

Respectfully submitted,

Richard D. Egan Reg. No. 36,788

Attorney for Applicant

O'KEEFE, EGAN & PETERMAN 1101 Capital of Texas Highway South Building C, Suite 200 Austin, Texas 78746 (512) 347-1611 FAX: (512) 347-1615

Enclosures

Form PTO-1449 (modified)		Atty. Docket No. Serial No.			
,		97-0008.02	Unknown		
List of Patents and Publications for Applicant's		Applicant			
		Bradley J. Howard			
INFORMATION DISCLOSURE S	TATEMENT				
		Filing Date:	Group:		
(Use several sheets if necessary)		Herewith	Unknown		
U.S. Patent Documents	Foreign Patent Documents		Other Art		
See Page 1	N/A		See Page 1		
- Joee Faye 1		IV/A	See Page 1		

U.S. Patent Documents

Exam. Init.	Ref. Des.	Document Number	Date	Name	Class	Sub Class	Filing Date if App.
	A 1	4,921,321	5/1/90	Weidman			
	A2	5,439,780	8/8/95	Joshi et al.			
-	A3	5,215,861	6/1/93	Augustino et al.			
	A4	4,978,594	12/18/90	Bruce et al.			
	A5	5,885,751	3/23/99	Weidman et al.			

Foreign Patent Documents

Exam. Init.	Ref. Des.	Document Number	Date	Country	Class	Sub Class	Translation Yes/No
	B1						

Other Art (Including Author, Title, Date Pertinent Pages, Etc.)

Exam. Init.	Ref. Des.	Citation				
	C1	Ajey M. Joshi et al., "Plasma Deposited Organosilicon Hydridge Network Polymers as Versatile Resists for Entirely Dry Mid-Deep UV Photolithography," SPIE, Vol. 1925, pp. 709-720, January 1993.				
	C2	O. Joubert et al., "Plasma polymerized – dry resist process for 0.25 µm photolithography," J. Vac. Sci. Technol. B 12(6), pp. 3909-3913, Nov/Dec 1994.				
	C3	O. Joubert et al., "Plasma Polymerized Organosilane Network Polymers; High Performance Resists for Positive and Negative Tone Deep UV Lithography," SPIE, Vol. 2195, pp. 358-371, May 1994.				
	C4	T. W. Weidman et al., Applications of Plasma Polymerized Methylsilane as a Resist and Silicon Dioxide Precursor for 193 and 248 nm Lithography," <i>SPIE</i> , Vol. 2438, pp. 496-512, June 1995.				
	C5	Timothy W. Weidman and Ajey M. Joshi, "New photodefinable glass etch masks for entirely dry photolithography: Plasma deposited organosilicon hydride polymers," <i>Appl. Phys. Lett.</i> 62(4), pp. 372-374, January 25, 1993				

Examiner:	Date Considered:				
LXAIIIIIIGI.	Date Considered:				

EXAMINER: initial if reference considered, whether or not citation is in conformance with MPEP609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.